SN74LVC2G241 **DUAL BUFFER/DRIVER** WITH 3-STATE OUTPUTS

SCES210K - APRIL 1999 - REVISED OCTOBER 2003

ην_{cc}

20E

6 🛛 1Y

2A

1Y

20E

Vcc

12A

8

7

5

DCT OR DCU PACKAGE

(TOP VIEW)

10E

1A 🛛

GND 🛛

GND

2Y

1A

1OE

2 2Y 🛛 3

4

YEA, YEP, YZA, OR YZP PACKAGE

(BOTTOM VIEW)

04 50

03 60

02 70

01 80

- Available in the Texas Instruments NanoStar[™] and NanoFree[™] Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 4.1 ns at 3.3 V
- Low Power Consumption, 10-µA Max Icc
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) <0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) >2 V at V_{CC} = 3.3 V, T_A = 25°C
- Ioff Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
 - ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

description/ordering information

选 3 注 3 本 A 5.5-VF This dual buffer/line driver is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G241 is designed specifically to improve both the performance and density of 3-state memory-address drivers, clock drivers, and bus-oriented receivers and transmitters.

ORDERING INFORMATION

TA	PACKAGE [†]	ORDERABLE PART NUMBER	TOP-SIDE MARKING [‡]		
−40°C to 85°C	NanoStar™ – WCSP (DSBGA) 0.17-mm Small Bump – YEA		SN74LVC2G241YEAR		
	NanoFree™ – WCSP (DSBGA) 0.17-mm Small Bump – YZA (Pb-free)		SN74LVC2G241YZAR		
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Reel of 3000	SN74LVC2G241YEPR	C2_	
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC2G241YZPR		
	SSOP – DCT	Reel of 3000	SN74LVC2G241DCTR	C41	
	VSSOP – DCU	Reel of 3000	SN74LVC2G241DCUR	C41	
	V330F - D00	Reel of 250	SN74LVC2G241DCUT	641_	

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

[‡]DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site. DCU: The actual top-side marking has one additional character that designates the assembly/test site. YEA/YZA, YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code,

and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition $(1 = SnPb, \bullet = Pb-free).$



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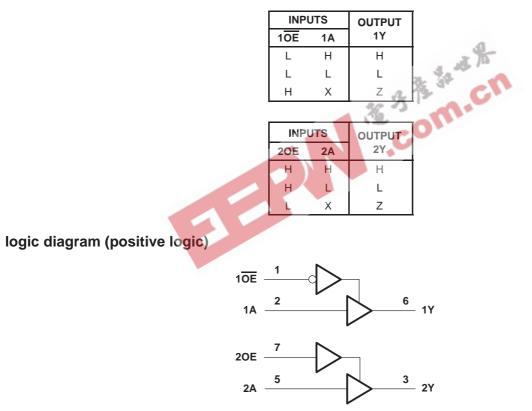
description/ordering information (continued)

NanoStar[™] and NanoFree[™] package technology is a major breakthrough in IC packaging concepts, using the die as the package.

The SN74LVC2G241 is organized as two 1-bit line drivers with separate output-enable $(1\overline{OE}, 2OE)$ inputs. When $1\overline{OE}$ is low and 2OE is high, the device passes data from the A inputs to the Y outputs. When $1\overline{OE}$ is high and 2OE is low, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor, and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking or the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.



Function Tables



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

	0 1	U	•	0 (,
					–0.5 V to 6.5 V
Input voltage range, V	/ _I (see Note 1)				–0.5 V to 6.5 V
Voltage range applied	to any output	in the high-im	pedance or pow	ver-off state, VO	
(see Note 1)					–0.5 V to 6.5 V
Voltage range applied	l to any output	in the high or	low state, V _O		
					$\dots -0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, I	$_{\rm K}(V_{\rm I} < 0)$.				–50 mA
Output clamp current,	$I_{OK} (V_O < 0)$				–50 mA
Continuous output cur	rrent, I _O				±50 mA
Continuous current the	rough V _{CC} or	GND			±100 mA
Package thermal impe	edance, θ _{.JA} (s	ee Note 3): D	CT package		220°C/W
	•	D	CU package		227°C/W
					140°C/W
		Y	EP/YZP packag	e	102°C/W
Storage temperature r	range, T _{stg}				–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not ay aft. در ceeded if. دing conditions tat. ordance with JESD 51. implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. The value of V_{CC} is provided in the recommended operating conditions table.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.



recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
		Operating	1.65	5.5		
V _{CC} Supply voltage	Supply voltage	Data retention only	1.5		V	
		V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$			
.,		V _{CC} = 2.3 V to 2.7 V	1.7			
VIH	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V	
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$			
		V _{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$		
		V _{CC} = 2.3 V to 2.7 V		0.7		
VIL	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V	
		$V_{CC} = 4.5 V \text{ to } 5.5 V$		$0.3 \times V_{CC}$		
VI	Input voltage	·	0	5.5	V	
		High or low state	0	V _{CC}	V	
VO Output voltage	Output voltage	3-state	0	5.5		
		V _{CC} = 1.65 V		-4		
		V _{CC} = 2.3 V	P	-8		
ЮН	High-level output current	2 34	A	-16	mA	
		$V_{CC} = 2.3 V$ $V_{CC} = 3 V$		-24	1	
		$V_{CC} = 4.5 V_{CC}$		-32		
		V _{CC} = 1.65 V		4		
		V _{CC} = 2.3 V		8	1	
IOL	Low-level output current			16	mA	
		$V_{CC} = 3 V$		24		
		V _{CC} = 4.5 V		32		
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20		
Δt/Δv	Input transition rise or fall rate	V _{CC} = 3.3 V ± 0.3 V	10			
		V _{CC} = 5 V ± 0.5 V		5	1	
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics	over	recommended	operating	free-air	temperature	range	(unless
otherwise noted)					-	•	

PARAMETER	TEST CONDITIONS	VCC	MIN	TYP†	MAX	UNIT
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} -0.1			
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2			
	I _{OH} = -8 mA	2.3 V	1.9			
VOH	I _{OH} = -16 mA		2.4			V
	$I_{OH} = -24 \text{ mA}$	3 V	2.3			
	I _{OH} = -32 mA	4.5 V	3.8			
	I _{OL} = 100 μA	1.65 V to 5.5 V			0.1	
	$I_{OL} = 4 \text{ mA}$	1.65 V			0.45	
	I _{OL} = 8 mA	2.3 V			0.3	
V _{OL}	I _{OL} = 16 mA				0.4 V	V
	I _{OL} = 24 mA	3 V			0.55	
	I _{OL} = 32 mA	4.5 V			0.55	
II A or Control inputs	VI = 5.5 V or GND	0 to 5.5 V			±5	μΑ
l _{off}	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}$	0			±10	μA
I _{OZ}	$V_{O} = 0 \text{ to } 5.5 \text{ V}$	3.6 V			10	μA
ICC	$V_{I} = 5.5 \text{ V or GND},$ $I_{O} = 0$	1.65 V to 5.5 V			10	μA
∆ICC	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μΑ
Ci	VI = V _{CC} or GND	3.3 V		3.5		pF
Co	V _O = V _{CC} or GND	3.3 V		6.5		pF

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25° C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

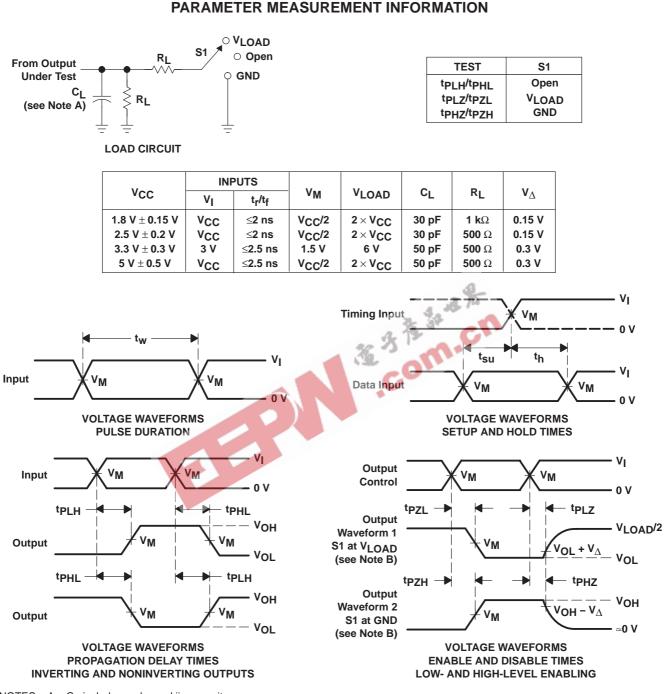
PARAMETER	FROM TO		V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	A	Y	3.3	8.8	1.5	4.8	1.4	4.3	1	3.7	ns
ten	OE	Y	4	9.9	1.9	5.6	1.2	4.7	1.2	3.8	ns
^t dis	OE	Y	1.5	11.6	1	5.8	1.4	4.4	1	3.4	ns
ten	OE	Y	3.2	8.8	1.5	4.7	1.6	4.1	1.1	3.3	ns
^t dis	OE	Y	1.7	12.5	1	5.2	1	4.2	1	3.3	ns

operating characteristics, $T_A = 25^{\circ}$

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V TYP	V _{CC} = 2.5 V TYP	V _{CC} = 3.3 V TYP	V _{CC} = 5 V TYP	UNIT
Power dissipation	Outputs enabled		19	19	20	22	pF
C _{pd} capacitance per buffer/driver	Outputs disabled	f = 10 MHz	2	2	2	3	



SN74LVC2G241 DUAL BUFFER/DRIVER WITH 3-STATE OUTPUTS SCES210K - APRIL 1999 - REVISED OCTOBER 2003



NOTES: A. CL includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as t_{dis}.
- F. tpzL and tpzH are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms





PACKAGE OPTION ADDENDUM

20-Sep-2005

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
74LVC2G241DCURE4	ACTIVE	US8	DCU	8	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
74LVC2G241DCURG4	ACTIVE	US8	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
74LVC2G241DCUTE4	ACTIVE	US8	DCU	8	250	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC2G241DCTR	ACTIVE	SM8	DCT	8	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC2G241DCUR	ACTIVE	US8	DCU	8	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC2G241DCUT	ACTIVE	US8	DCU	8	250	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC2G241YEAR	ACTIVE	WCSP	YEA	8	3000	TBD	SNPB	Level-1-260C-UNLIM
SN74LVC2G241YEPR	ACTIVE	WCSP	YEP	8	3000	TBD	SNPB	Level-1-260C-UNLIM
SN74LVC2G241YZAR	ACTIVE	WCSP	YZA	8	3000	Pb-Free (RoHS)	SNAGCU	Level-1-260C-UNLIM
SN74LVC2G241YZPR	ACTIVE	WCSP	YZP	8	3000	Pb-Free (RoHS)	SNAGCU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details. **TBD:** The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

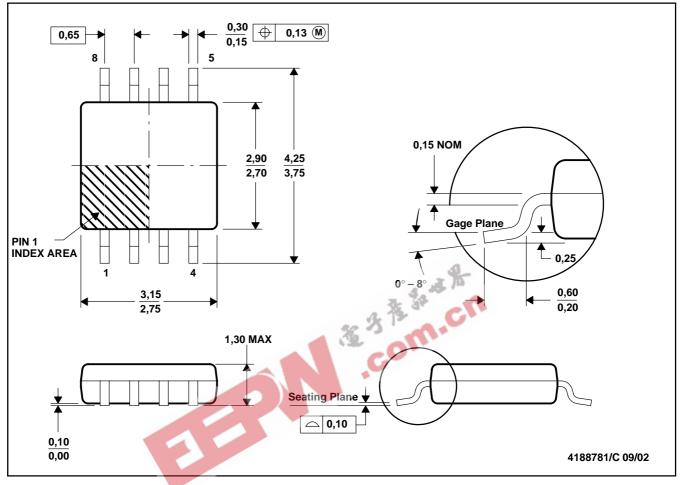
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MECHANICAL DATA

MPDS049B - MAY 1999 - REVISED OCTOBER 2002

PLASTIC SMALL-OUTLINE PACKAGE

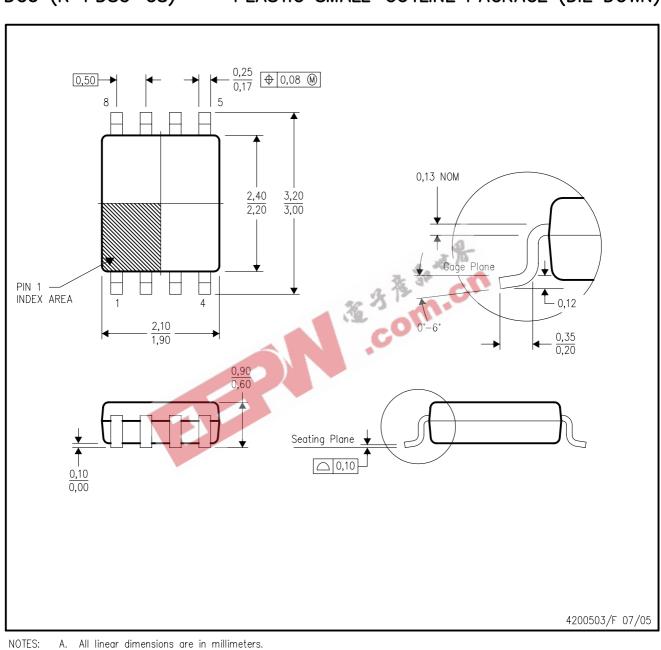


NOTES: A. All linear dimensions are in millimeters.

DCT (R-PDSO-G8)

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.





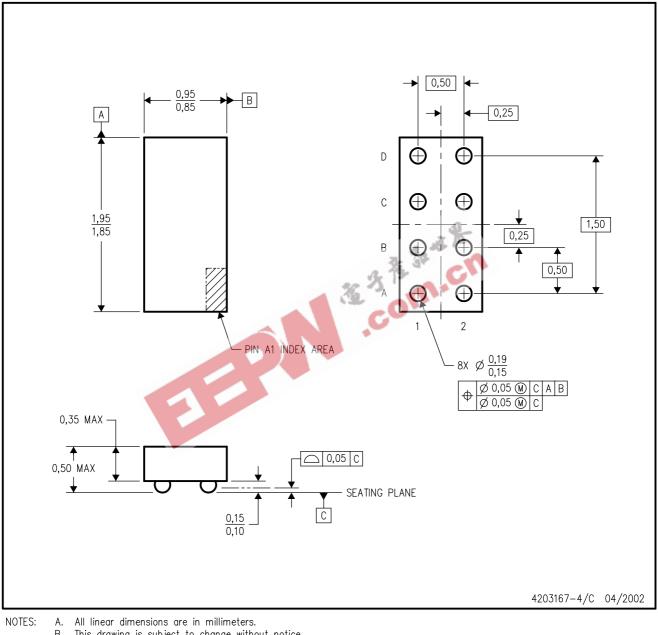
DCU (R-PDSO-G8) PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)

- Β. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-187 variation CA.



YEA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



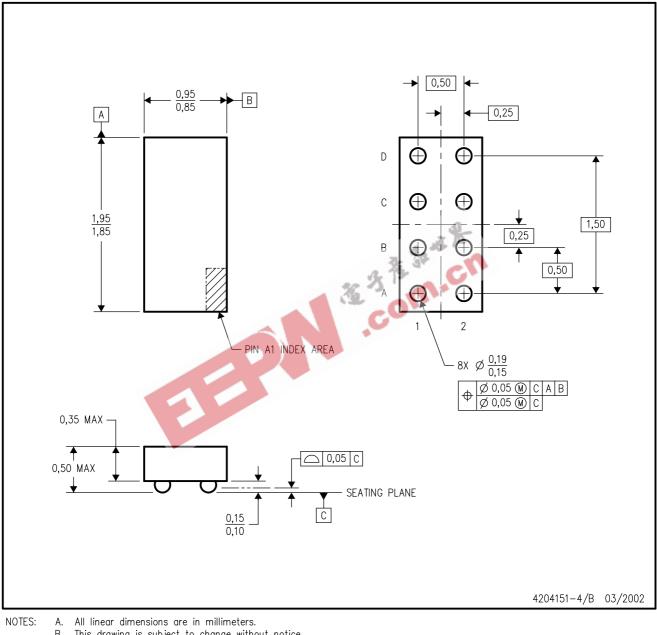
- B. This drawing is subject to change without notice.C. NanoStar™ package configuration.
- D. Package complies to JEDEC MO-211 variation EB.
- E. This package is tin-lead (SnPb). Refer to the 8 YZA package (drawing 4204151) for lead-free.

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YZA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



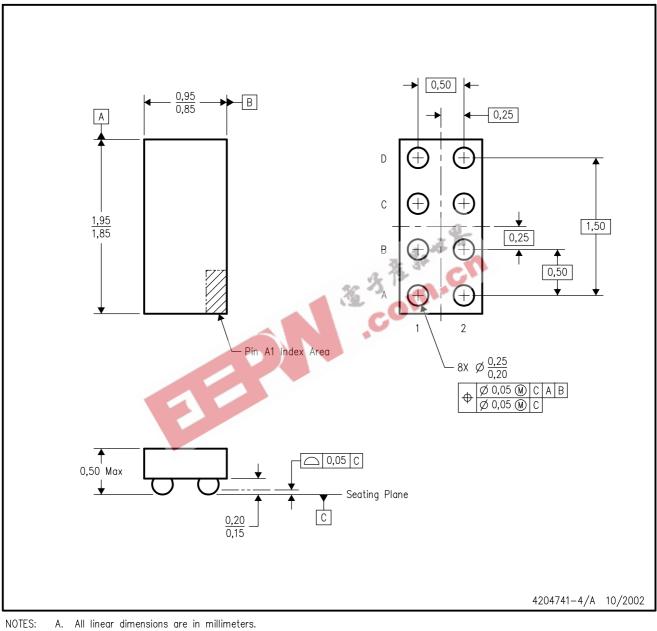
- B. This drawing is subject to change without notice.C. NanoFree™ package configuration.
- Package complies to JEDEC MO-211 variation EB. D.
- E. This package is lead-free. Refer to the 8 YEA package (drawing 4203167) for tin-lead (SnPb).

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YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



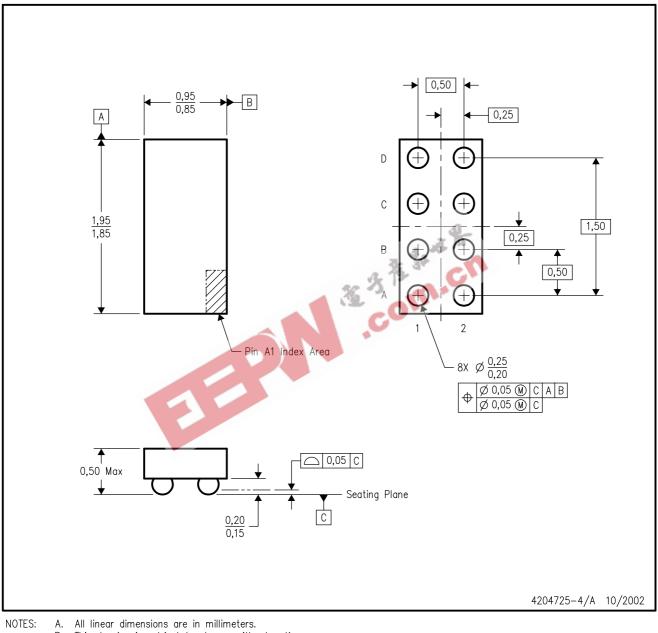
- B. This drawing is subject to change without notice.C. NanoFree™ package configuration.
- D. This package is lead-free. Refer to the 8 YEP package (drawing 4204725) for tin-lead (SnPb).

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YEP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



B. This drawing is subject to change without notice.C. NanoStar™ package configuration.

- D. This package is tin-lead (SnPb). Refer to the 8 YZP package (drawing 4204741) for lead-free.

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Mailing Address:

Texas Instruments

Post Office Box 655303 Dallas, Texas 75265

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